



Product Overview

SGS10N60RUFDTU: IGBT, 600V, 10A, Short Circuit Rated

For complete documentation, see the data sheet.

ON Semiconductor's RUFDT series of Insulated Gate Bipolar Transistors(IGBTs) provide low conduction and switching losses as well as short circuit ruggedness. The RUFDT series is designed for applications such as motor control, UPS and general inverters where short circuit ruggedness is a required feature.

Features

- 10A, 600V, TC = 100°C
- Low saturation voltage: $V_{CE(sat)} = 2.2V @ I_C = 10A$
- Typical Fall Time.242ns at $T_J = 125^\circ C$
- High Speed Switching
- High input impedance
- Short Circuit Rating

Applications

- Motion Control - Home Appliance

Part Electrical Specifications																	
Product	Pricing (\$/Unit)	Compliance	Status	V_{CES} Typ (V)	I_C Max (A)	$V_{CE(sat)}$ Typ (V)	V_F Typ (V)	E_{off} Typ (mJ)	E_{on} Typ (mJ)	T_{rr} Typ (ns)	I_{rr} Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand (μs)	E_{AS} Typ (mJ)	P_D Max (W)	Co-Packaged Diode	Package Type
SGS10N60RUFDTU	1.344	Pb-free	Active	600	10	2.2	1.4	0.215	0.141	60	3.5	30	10	-	55	Yes	TO-220-3 FullPak

For more information please contact your local sales support at www.onsemi.com.

Created on: 4/6/2020